

Name:

Student ID Number:

Section Number: 01A

Lecturer: Prof Md Zaini & Dr Jamaludin

Table Number:



College of Engineering
Department of Electrical Engineering

Midterm Test

SEMESTER 3, ACADEMIC YEAR 2018/2019

Subject Code : **EEEB273**
Course Title : **Electronics Analysis & Design II**
Date : **5 April 2019**
Duration : **2 hours**

Instructions to the candidates:

1. Write your **Name** and **Student ID Number**.
2. **Write all your answers using pen. DO NOT USE PENCIL** except for the diagram.
3. **ANSWER ALL QUESTIONS.** Show clearly all your calculations. Every value **must** be written with its correct Unit.
4. **WRITE YOUR ANSWER ON THIS QUESTION PAPER.**

NOTE: DO NOT OPEN THE QUESTION PAPER UNTIL INSTRUCTED TO DO SO.

☺ **GOOD LUCK!** ☺

Question Number	Q1 (a)	Q1 (bcd)	Q2 (abc)	Q3 (ab)	Q4 (ab)	Total
Marks						
CO	9	1	3	1	2	

BASIC FORMULA FOR TRANSISTOR

BJT

$$i_C = I_S e^{v_{BE}/V_T}; \text{nnp}$$

$$i_C = I_S e^{v_{EB}/V_T}; \text{pnp}$$

$$i_C = \alpha i_E = \beta i_B$$

$$i_E = i_B + i_C$$

$$\alpha = \frac{\beta}{\beta + 1}$$

; Small signal

$$\beta = g_m r_\pi$$

$$g_m = \frac{I_{CQ}}{V_T}$$

$$r_\pi = \frac{\beta V_T}{I_{CQ}}$$

$$r_o = \frac{V_A}{I_{CQ}}$$

$$V_T = 26 \text{ mV}$$

Quadratic formula :

$$Ax^2 + Bx + C = 0 \quad \rightarrow \quad x = \frac{-B \pm \sqrt{B^2 - 4AC}}{2A}$$

MOSFET

; N – MOSFET

$$v_{DS}(\text{sat}) = v_{GS} - V_{TN}$$

$$i_D = K_n [v_{GS} - V_{TN}]^2$$

$$K_n = \frac{k'_n}{2} \cdot \frac{W}{L}$$

; P – MOSFET

$$v_{SD}(\text{sat}) = v_{SG} + V_{TP}$$

$$i_D = K_p [v_{SG} + V_{TP}]^2$$

$$K_p = \frac{k'_p}{2} \cdot \frac{W}{L}$$

; Small signal

$$g_m = 2\sqrt{K_n I_{DQ}} \quad ; \text{N - MOSFET}$$

$$g_m = 2\sqrt{K_p I_{DQ}} \quad ; \text{P - MOSFET}$$

$$r_o \cong \frac{1}{\lambda I_{DQ}}$$

This is extra page for answers. Please indicate question number clearly.

QUESTION 1 [25 marks]

You are required to **design** a **Widlar** current source using **NPN** transistors such that $I_{REF} = 2 \text{ mA}$ and $I_O = 50 \text{ }\mu\text{A}$. Let $V^+ = 15 \text{ V}$ and $V^- = 0 \text{ V}$. The transistors are matched and $V_{BE} = 0.7 \text{ V}$ at 1 mA .

- (a) **Draw** the circuit and **clearly label** all the resistors and transistors. **[4 marks]**
- (b) **Derive** the I_{REF} and I_O relationship of the circuit, showing all your steps in getting the relationship. **[6 marks]**
- (c) **Design** the circuit and **clearly show all calculations** as marks are given according to this. **[10 marks]**
- (d) Given V_A and β for Q_2 is **100 V** and **50** respectively, **determine** the output resistance, R_O , of the **Widlar** current source. **[5 marks]**

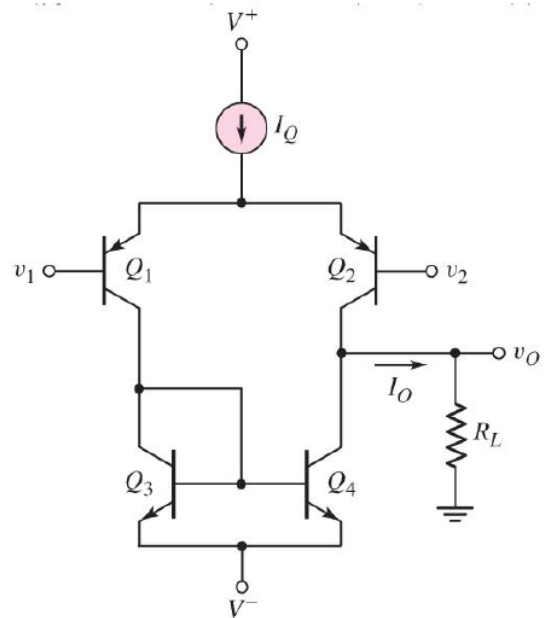
Answers for Question 1

Answers for Question 1 (Continued)

QUESTION 2 [25 marks]

Figure 1 shows a differential amplifier has a pair of **PNP** bipolar as **input devices** and a pair of **NPN** bipolar connected as an **active load**. The circuit has $I_Q = 0.2 \text{ mA}$ bias current and the transistor parameters are $\beta = 100$ and $V_A = 100 \text{ V}$.

- (a) Calculate I_O such that the **DC currents** in the diff-amp are **balanced**. [6 marks]
 (b) Determine the **open-circuit** differential-mode voltage gain, A_d . [12 marks]
 (c) Find the differential-mode voltage gain if a load resistance $R_L = 250 \text{ k}\Omega$ is connected to the output. [7 marks]

Answers for Question 2**Figure 1**

Answers for Question 2 (Continued)

QUESTION 3 [25 marks]

For a MOSFET current source circuit shown in **Figure 2**, transistor parameters are $V_{TN} = 0.7 \text{ V}$, $k'_n = 70 \mu\text{A}/\text{V}^2$, and $\lambda = 0.015 \text{ V}^{-1}$. The transistor aspect ratios are $(W/L)_1 = 20$, $(W/L)_2 = 12.5$, and $(W/L)_3 = 3$.

- (a) Determine V_{GS1} , V_{GS3} , I_{REF} , I_O , and V_{DS2} [15 marks]
- (b) Find I_O at $V_{DS2} = 2.5 \text{ V}$ [10 marks]

Answers for Question 3

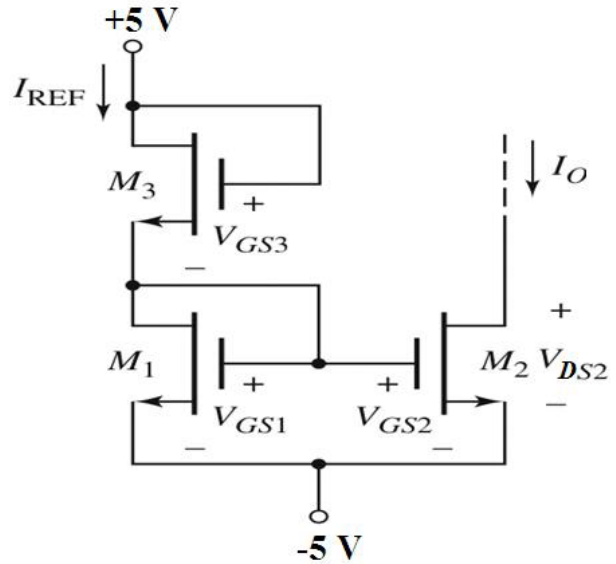


Figure 2

Answers for Question 3 (Continued)

QUESTION 4 [25 marks]

Consider the diff-amp shown in **Figure 3**. The transistor parameters are: $K_{n1} = K_{n2} = 0.1 \text{ mA/V}^2$ and $K_{n3} = K_{n4} = 0.3 \text{ mA/V}^2$. Other parameters for all transistors are $\lambda = 0$ and $V_{TN} = 1 \text{ V}$.

- (a) Find the values of $I_1, I_Q, V_{GS4}, V_{GS2}, v_{O1}$, and v_{O2} . [15 marks]
- (b) Determine the maximum range of the common-mode input voltage, i.e. find the values for $v_{CM}(\text{max})$ and $v_{CM}(\text{min})$. [10 marks]

Answers for Question 4

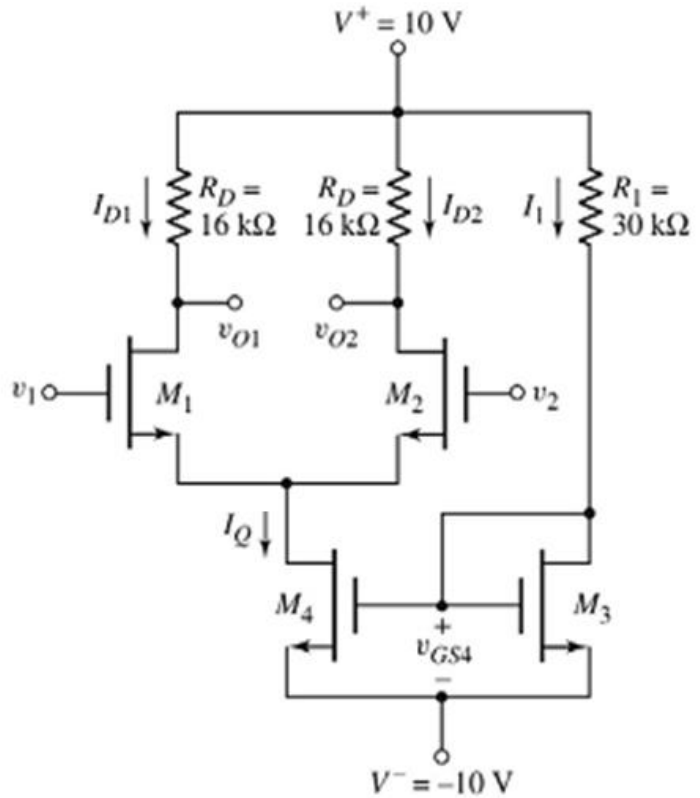


Figure 3

Answers for Question 4 (Continued)

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